

Fig. 1

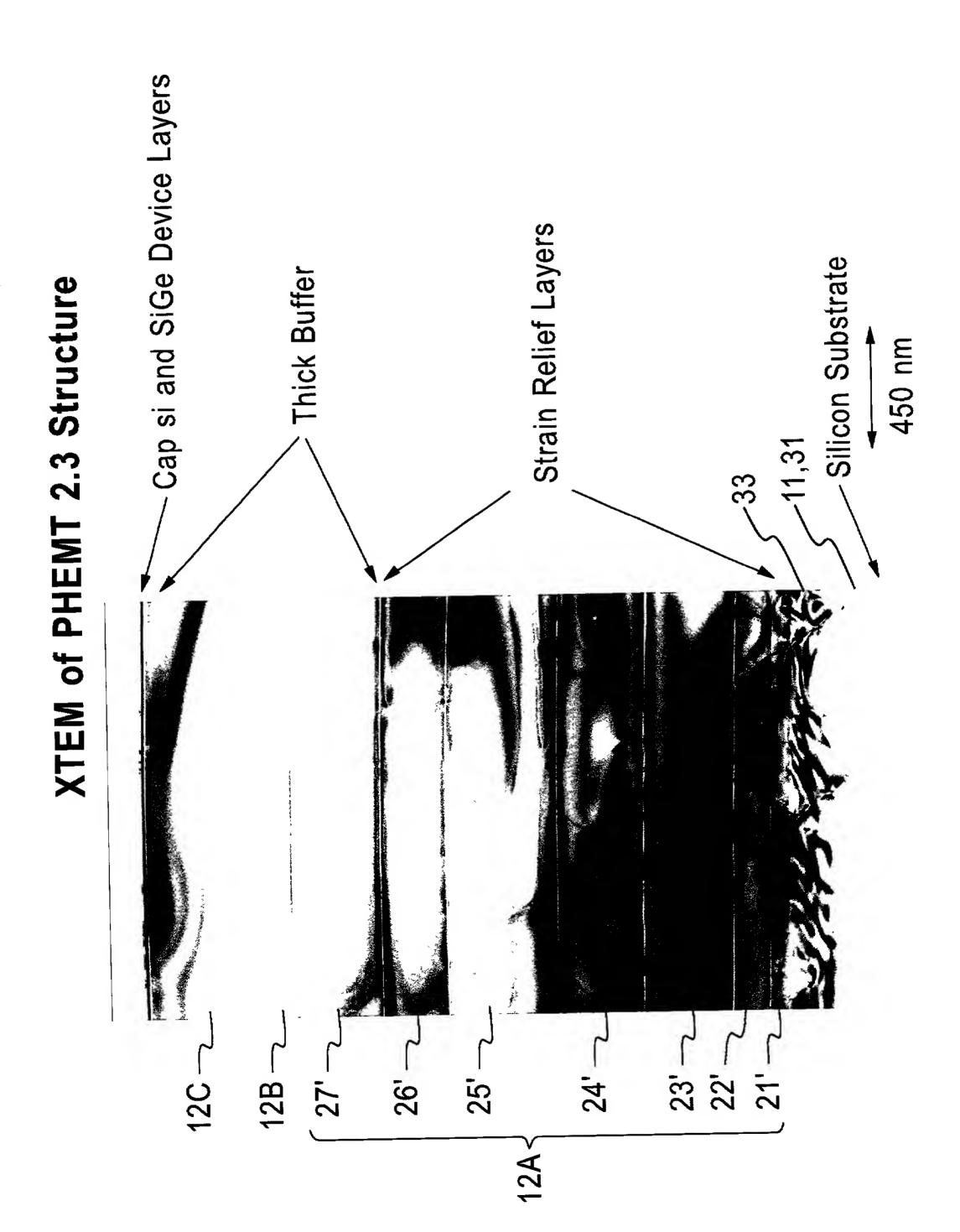
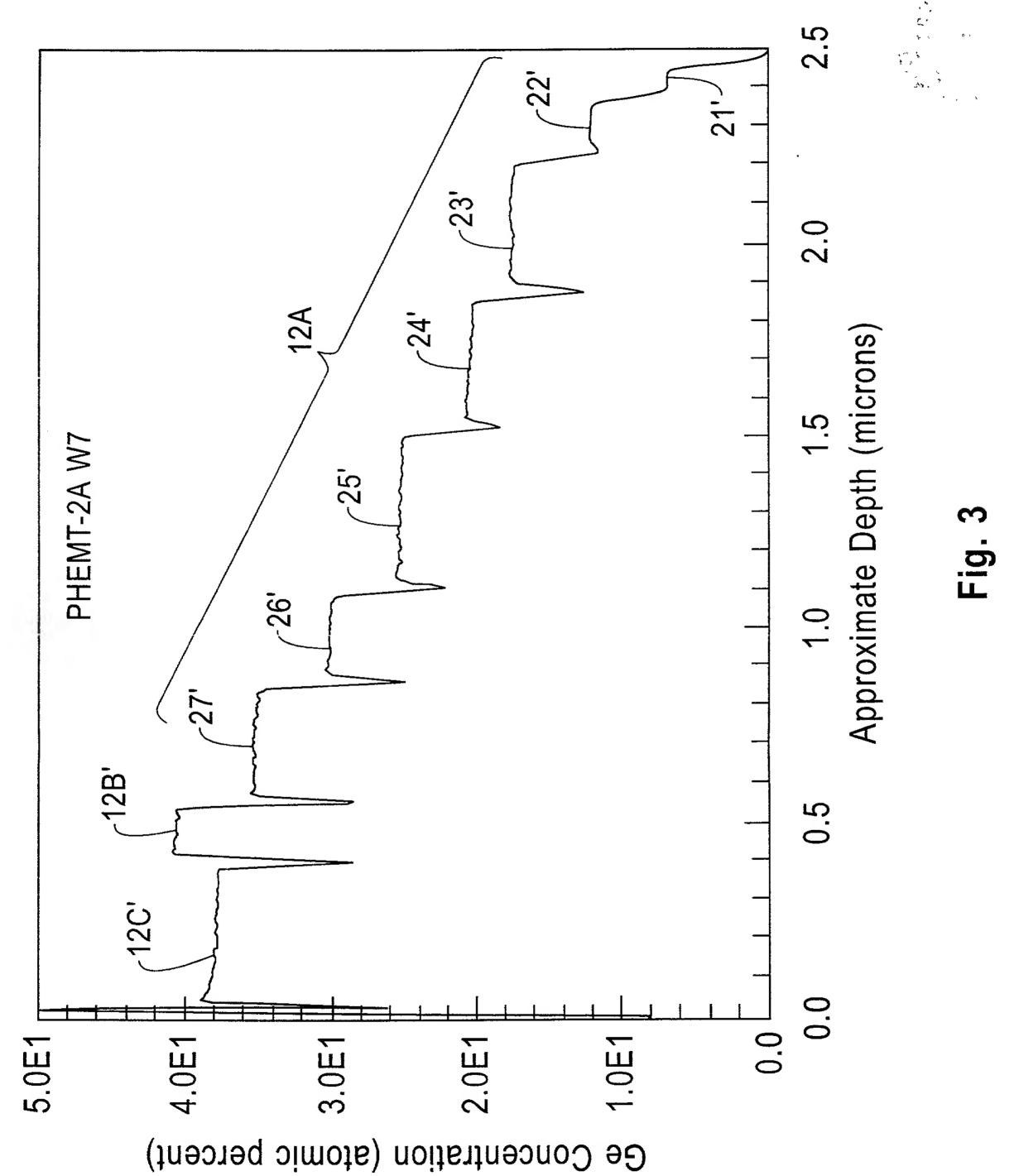


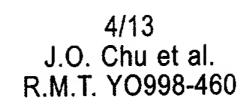
Fig. 2

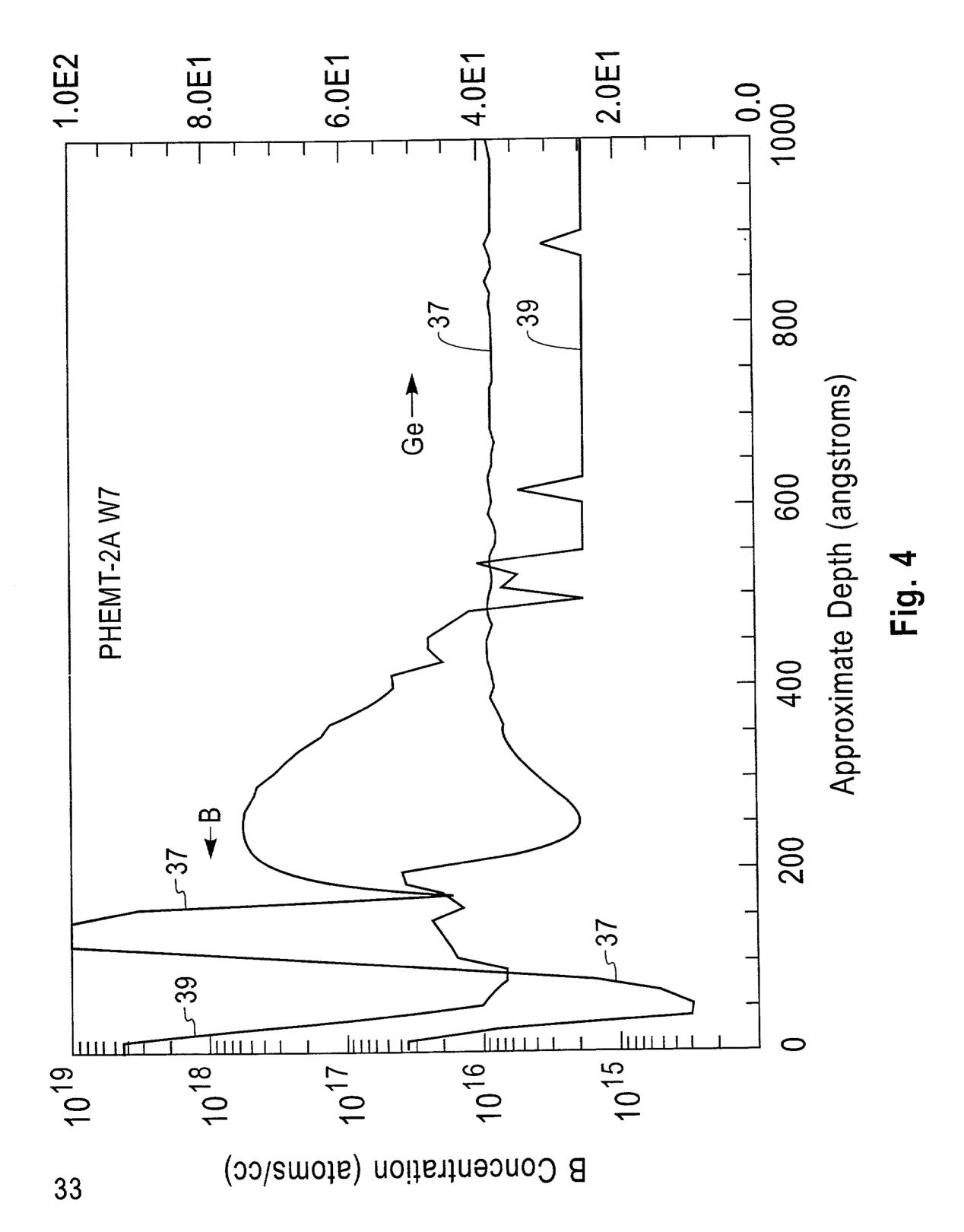
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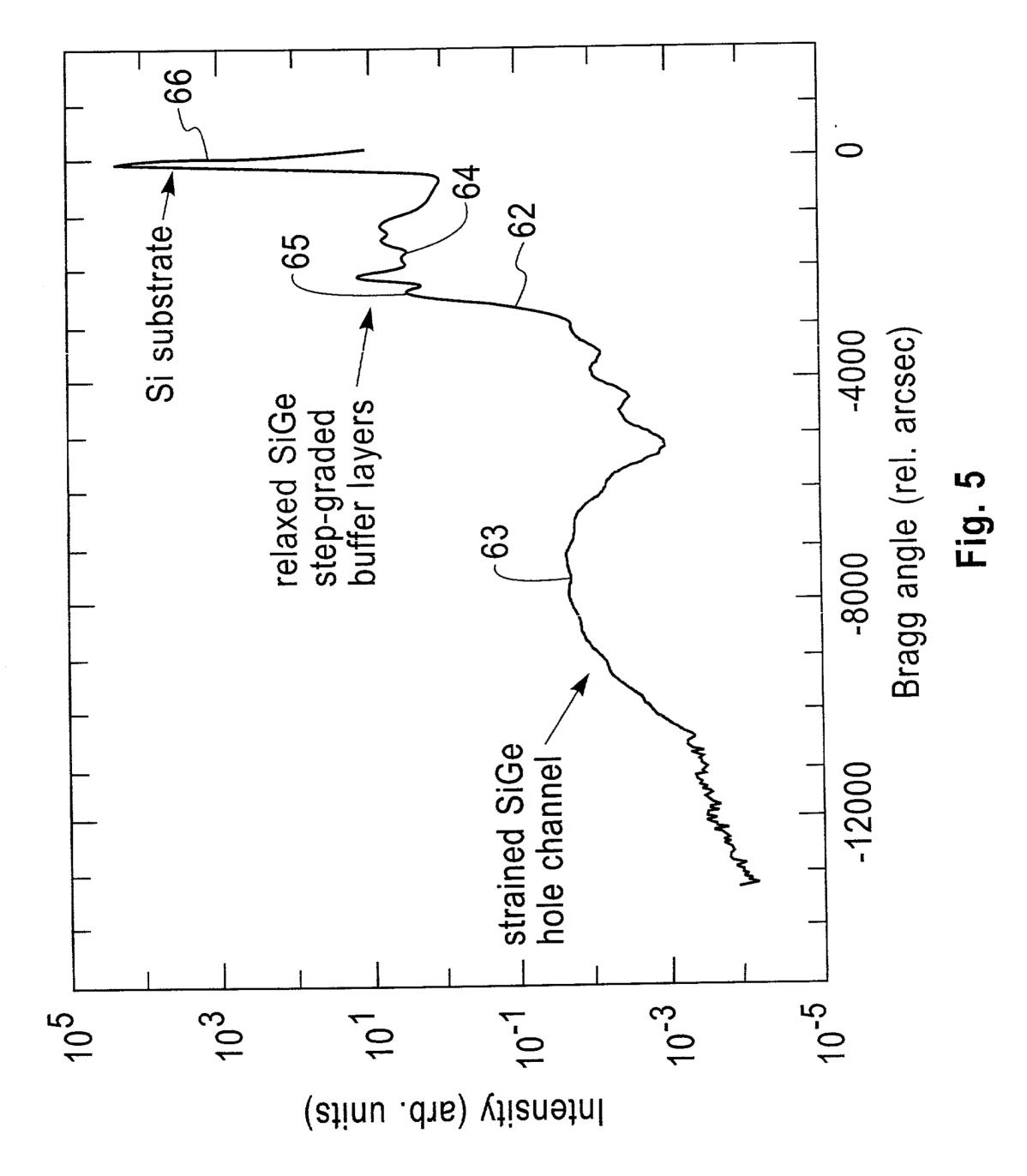
Amp, there may, at the made



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15/  $\frac{2}{8}$ XTEM of PHEMT 2.3 Device 25 nm Cap Si and SiGe and Supply Layer Thick Buffer

Fig. 6

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Stacking fault densities ~ 10<sup>6</sup> - 10<sup>8</sup>/cm<sup>2</sup>

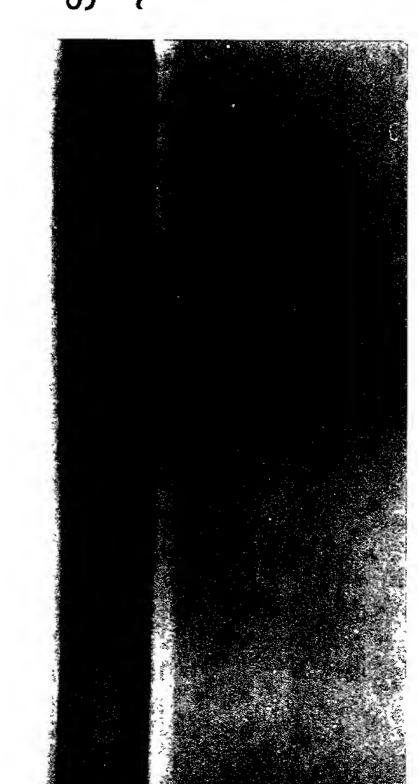


Fig.

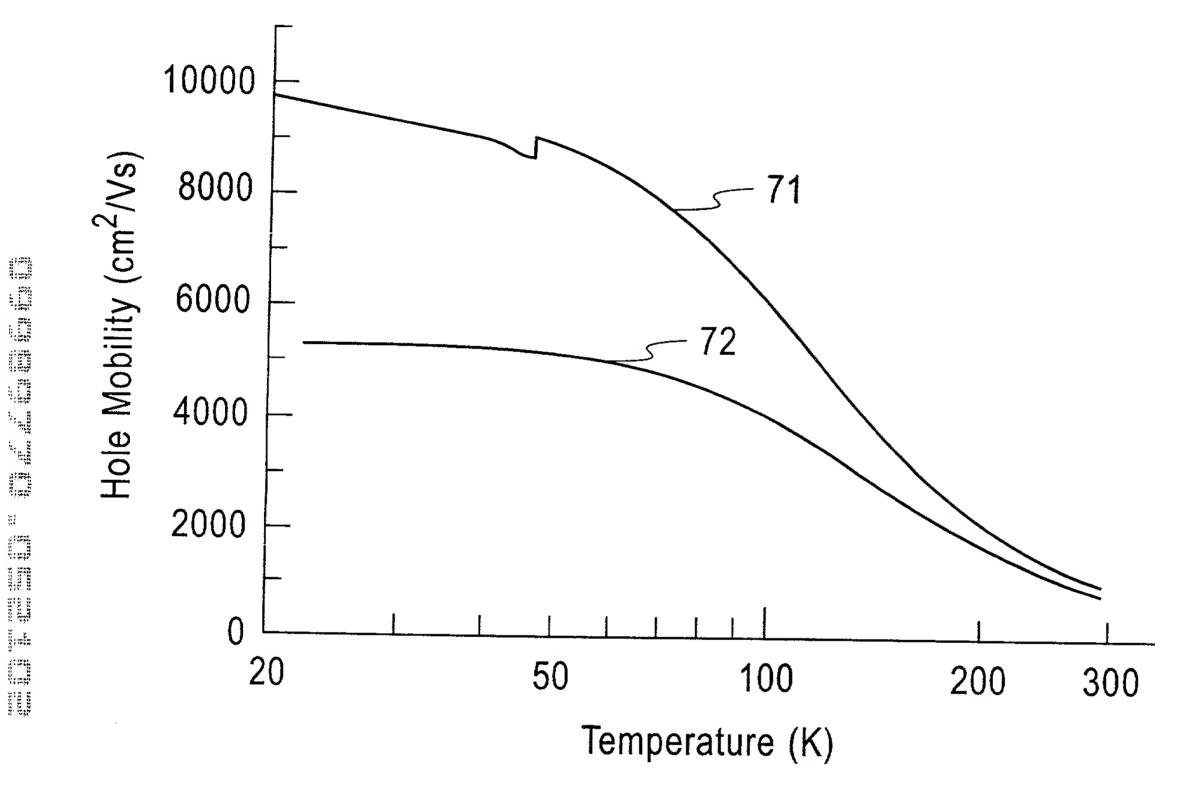


Fig. 8

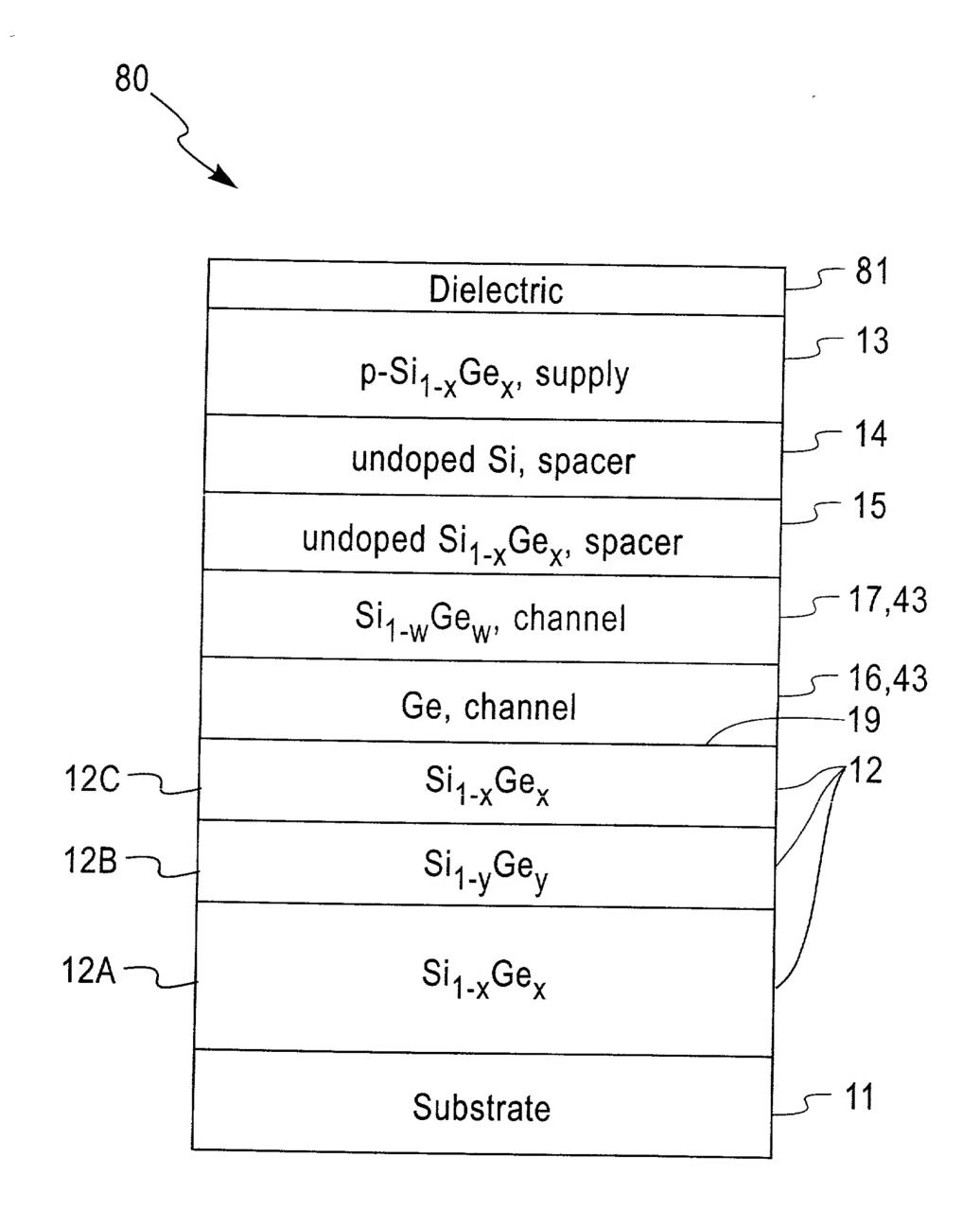
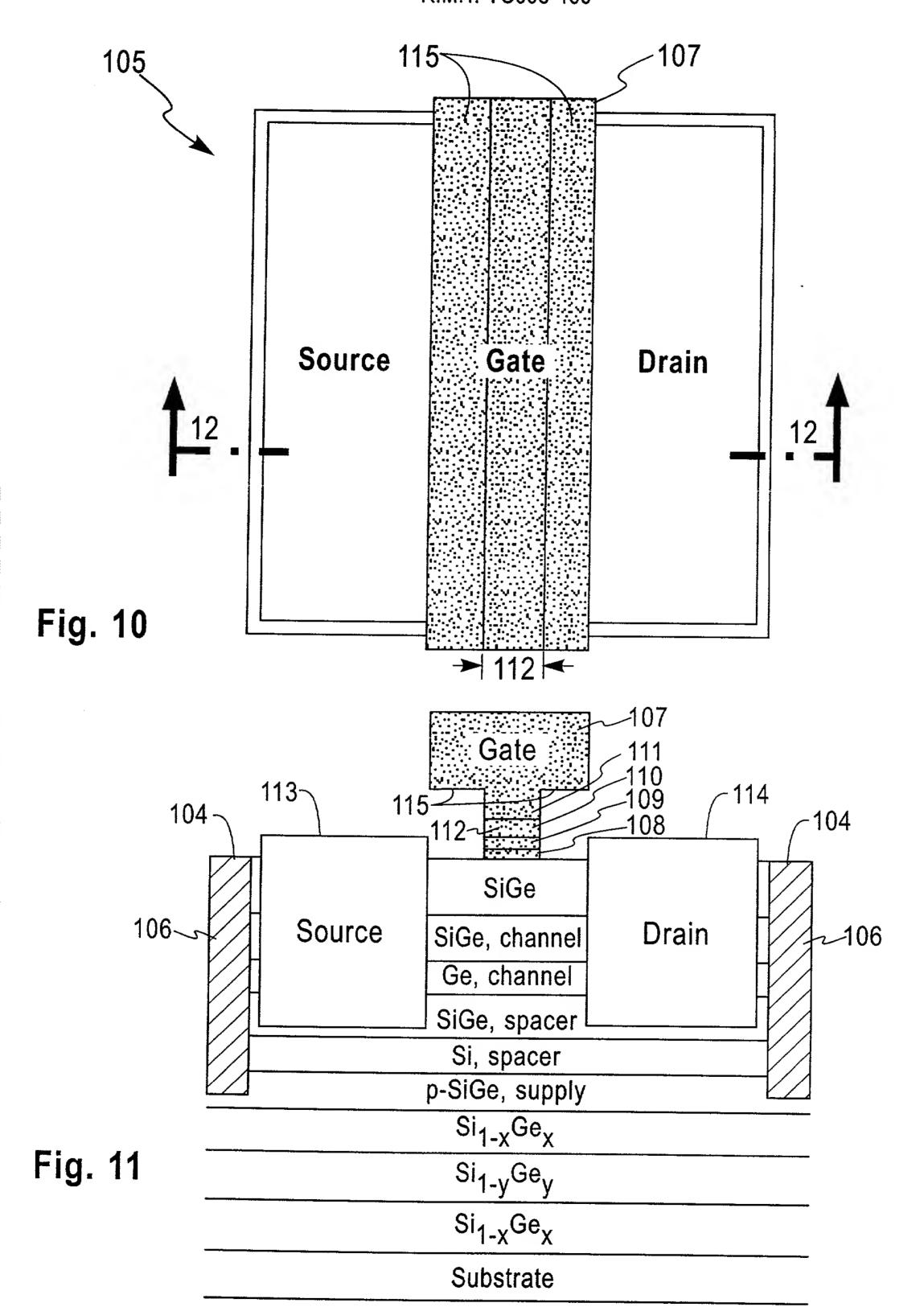


Fig. 9

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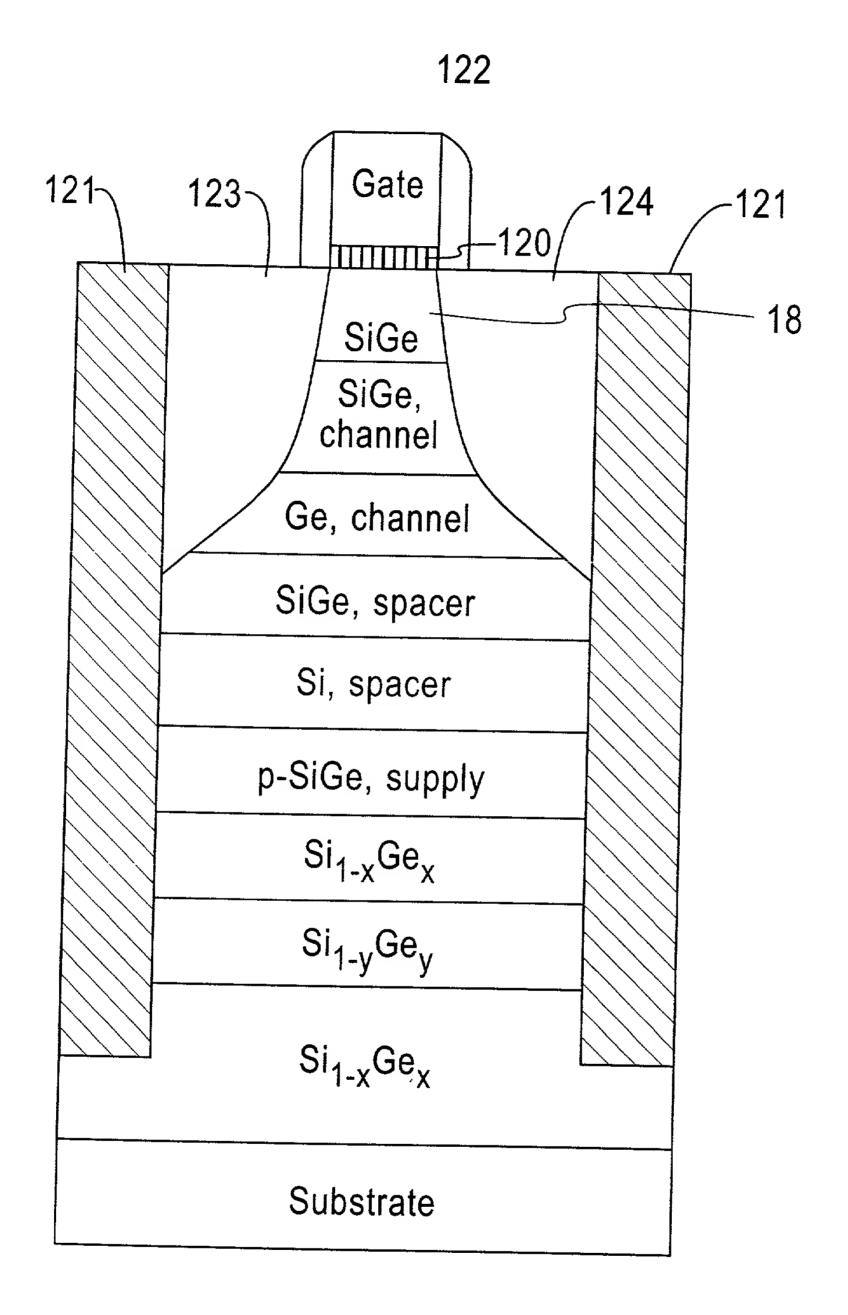


Fig. 12

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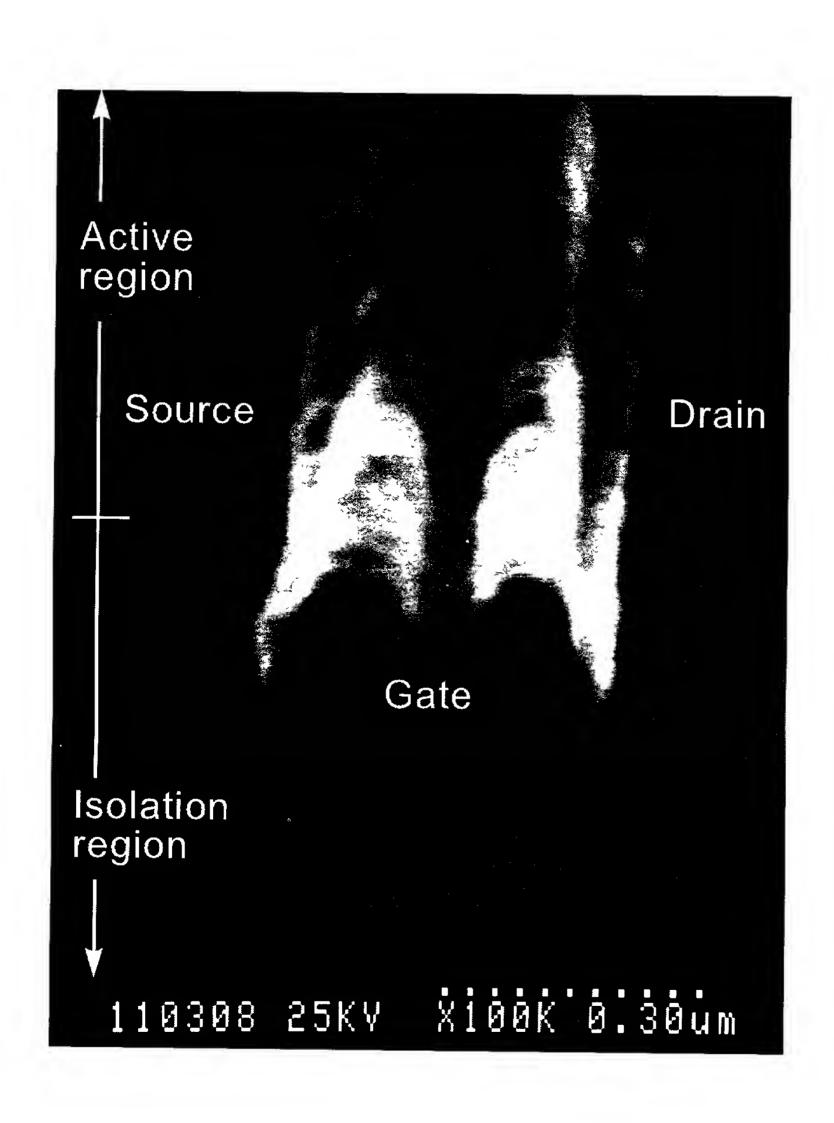


Fig. 13

p-type composite-channel MODFET,  $L_g$  = 0.09 $\mu$ m, W = 25 $\mu$ m

